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A. Frazzetto; F. Giannazzo; P. Fiorenza; V. Raineri; F. Roccaforte

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This article was originally published online on 19 August 2011 with an incorrect version of Fig. 4. AIP apologizes for this error.

The figure was correct as it appeared in the printed version of the article. All online versions of the article were corrected on 23 August 2011.

[1]A. Frazzetto, F. Giannazzo, P. Fiorenza, V. Raineri, and F. Roccaforte, Appl. Phys. Lett. **99**, 072117 (2011).

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